L Number	Hits	Search Text	DB	Time stamp
1	77763	414/\$.ccls.	USPAT;	2003/11/25 12:27
			US-PGPUB;	
i i			EPO; JPO;	
			DERWENT;	
	410	AAA/A ala aa la	IBM_TDB	
2	416	414/\$.ccls. and ((die or chip or substrate or semiconductor)	USPAT;	2003/11/25 13:08
		near3 (bond\$4 or stack\$4))	US-PGPUB;	
			EPO; JPO; DERWENT:	
			IBM TDB	
3	291	414/\$.ccls. and ((die or chip or semiconductor) near3	USPAT;	2003/11/25 12:30
]		(bond\$4 or stack\$4))	US-PGPUB:	2000/11/20 12:00
į į		, , , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
			DERWENT:	
))	1		IBM_TDB	
4	11	, , , , , , , , , , , , , , , , , , ,	USPAT;	2003/11/25 12:31
		(bond\$4 or stack\$4))) and (introduc\$4 near3 wafer)	US-PGPUB;	
1			EPO; JPO;	
[DERWENT;	
_	00700		IBM_TDB	
5	80782	((die or chip or semiconductor) near3 (bond\$4 or stack\$4))	USPAT;	2003/11/25 12:30
			US-PGPUB;	
			EPO; JPO; DERWENT;	
1	i		IBM_TDB	
6	278	(((die or chip or semiconductor) near3 (bond\$4 or stack\$4)))	USPAT;	2003/11/25 12:31
	2,0	and (introduc\$4 near3 wafer)	US-PGPUB;	2000/11/20 12:01
!		and (miles also maile)	EPO; JPO;	
			DERWENT;	
]			IBM_TDB	
7	0	((((die or chip or semiconductor) near3 (bond\$4 or stack\$4)))	USPAT;	2003/11/25 12:31
		and (introduc\$4 near3 wafer)) and ((introduc\$4 near3 wafer)	US-PGPUB;	
		with (stacker or bonder))	EPO; JPO;	
			DERWENT;	
		((inter-decay) = === () === () === () === ()	IBM_TDB	0000/44/05 40:00
8	0	((introduc\$4 near3 wafer) with (stacker or bonder))	USPAT; US-PGPUB;	2003/11/25 12:32
,			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
9	325	(wafer with (stacker or bonder))	USPAT;	2003/11/25 12:32
		·	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
40	255		IBM_TDB	00004457 17.55
10	252	((wafer with (stacker or bonder))) and ((die or chip or	USPAT;	2003/11/25 13:08
	(substrate or semiconductor) near3 (bond\$4 or stack\$4))	US-PGPUB;	
	ĺ		EPO; JPO;	
1	ì		DERWENT; IBM_TDB	
11	672	438/455.ccls.	USPAT;	2003/11/25 13:08
	7,2		US-PGPUB;	
			EPO; JPO;	
	ļ		DERWENT;	
	ı		IBM_TDB	
12	484	438/455.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 13:52
[ļ	semiconductor) near3 (bond\$4 or stack\$4))	US-PGPUB;	
			EPO; JPO;	
	Ì		DERWENT;)
			IBM_TDB	

40	7 447			T
13	117	438/455.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 13:43
		semiconductor) near3 (stack\$4))	US-PGPUB;	
			EPO; JPO;	
ļ	1		DERWENT;	ļ
			IBM_TDB	
14	0	(((carrying or carried or convey\$4 or transfer\$4 or introduc\$4	USPAT;	2003/11/25 13:48
		or transport\$4) near4 wafer) with ((into or inside or in) near3	US-PGPUB;	
	1	(bonder or stacker)))	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
15	38706	((carrying or carried or convey\$4 or transfer\$4 or introduc\$4	USPAT:	2003/11/25 13:47
		or transport\$4) near4 wafer)	US-PGPUB;	2000/11/20 10:4/
	1	or managerity in our invariance	EPO; JPO;	
			DERWENT:	
1			IBM_TDB	
16	42831	((carrying or carried or convey\$4 or transfer\$4 or introduc\$4	USPAT;	2003/11/25 13:47
1 10	72051	or transport\$4) near4 wafer)	'	2003/11/25 13.47
		or transports4) hear4 water)	US-PGPUB;	
			EPO; JPO;	
1	Ì		DERWENT;	
47	4.0		IBM_TDB	
17	16	(((carrying or carried or convey\$4 or transfer\$4 or introduc\$4	USPAT;	2003/11/25 13:51
1		or transport\$4) near4 wafer)) and ((into or inside or in)	US-PGPUB;	
		near3 (bonder or stacker))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
18	491	438/109.ccls.	USPAT;	2003/11/25 13:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
19	288	438/109.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 13:52
		semiconductor) near3 stack\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT:	
1			IBM_TDB	
20	16	(438/109.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 13:52
		semiconductor) near3 stack\$4)) and (bonder or stacker)	US-PGPUB:	
		(EPO; JPO;	
			DERWENT:	
			IBM TDB	
21	8	(US-6560857-\$ or US-5979739-\$ or US-6566232-\$ or	USPAT:	2003/11/25 13:56
1		US-6177296-\$).did. or (US-20030145939-\$ or	US-PGPUB	2000, 11,20 10.00
		US-20020092622-\$ or US-20010013643-\$ or	30, 3, 35	
1		US-20030106209-\$).did.		
22	14	(US-6514795-\$ or US-6337227-\$ or US-6620651-\$ or	USPAT;	2003/11/25 13:56
	'-7	US-6506664-\$ or US-6376265-\$ or US-6165815-\$ or	US-PGPUB	2000/11/20 10.00
		US-5952725-\$ or US-3591921-\$ or US-6617198-\$ or	00-1-00	
]	US-5804004-\$ or US-6428641-\$).did. or (US-20020004288-\$		
	ļ	or US-20030060034-\$ or US-20020185704-\$).did.		
23		(US-5979739-\$ or US-6620651-\$ or US-5952725-\$ or	LICDAT	2002/44/25 44:24
23	6		USPAT;	2003/11/25 14:24
		US-5804004-\$ or US-3591921-\$).did. or	US-PGPUB	
	142700	(US-20010013643-\$).did.	LICDAT	0000/40/40 44:04
-	143799	438/\$.ccls.	USPAT;	2003/10/18 14:21
			US-PGPUB;	
1	1		EPO; JPO;	
	<u> </u>		DERWENT;	
		400.00	IBM_TDB	
-	3103	438/\$.ccls. and (die near4 bond\$4)	USPAT;	2003/10/18 14:27
			US-PGPUB;	
	j		EPO; JPO;	
]]		DERWENT;	
	l		IBM_TDB	

	246	(429/C cole and (diament hand (4)) and (date 104) and	LIODAT:	1 0000404040
-	346	(438/\$.ccls. and (die near4 bond\$4)) and (stack\$4 near4 (chip or die or device or semiconductor))	USPAT; US-PGPUB;	2003/10/18 14:27
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	8	((438/\$.ccls. and (die near4 bond\$4)) and (stack\$4 near4	USPAT;	2003/10/18 14:27
		(chip or die or device or semiconductor))) and (die near3	US-PGPUB;	
		bonder)	EPO; JPO;	
			DERWENT;	
_	104030	156/\$.ccls.	IBM_TDB	2003/10/18 14:27
	104000	10074.0013.	USPAT; US-PGPUB;	2003/10/16 14.2/
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
-	733	156/\$.ccls. and (die near4 bond\$4)	USPAT;	2003/10/18 14:27
ļ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1		(450/0	IBM_TDB	0000404040
-	29	(156/\$.ccls. and (die near4 bond\$4)) and (stack\$4 near4 (chip or die or device or semiconductor))	USPAT; US-PGPUB:	2003/10/18 14:31
		(Crip of the of device of Serficonductor))	EPO; JPO;	
l	l		DERWENT:	
			IBM TDB	
-	4231	438/106,109,113,114,118,119.ccls.	USPAT;	2003/10/18 15:19
]		US-PGPUB;	
			EPO; JPO;	
	ľ		DERWENT;	
	47500	(IBM_TDB	000040404044
-	17583	(carrying or introducing) same wafer	USPAT; US-PGPUB;	2003/10/18 14:34
	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	132	438/106,109,113,114,118,119.ccls. and ((carrying or	USPAT;	2003/10/18 14:35
}		introducing) same wafer)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	14	(438/106,109,113,114,118,119.ccls. and ((carrying or	IBM_TDB USPAT;	2003/10/18 14:42
i -	· · ·	introducing) same wafer)) and (((carrying or introducing)	US-PGPUB;	2000/10/10 14.42
		same wafer) same (die near4 bond\$4))	EPO; JPO;	
]		DERWENT;	
	1		IBM_TDB	
-	77	(((carrying or introducing) same wafer) same (die near4	USPAT;	2003/10/18 14:42
]	bond\$4))	US-PGPUB;	
			EPO; JPO; DERWENT;	
	ļ		IBM_TDB	
_	63	((((carrying or introducing) same wafer) same (die near4	USPAT:	2003/10/18 14:42
		bond\$4))) not ((438/106,109,113,114,118,119.ccls. and	US-PGPUB;	
		((carrying or introducing) same wafer)) and (((carrying or	EPO; JPO;	
		introducing) same wafer) same (die near4 bond\$4)))	DERWENT;	
	4.5		IBM_TDB	2002/40/40 44:50
-	15	(((((carrying or introducing) same wafer) same (die near4 bond\$4))) not ((438/106,109,113,114,118,119.ccls. and	USPAT; US-PGPUB;	2003/10/18 14:59
		((carrying or introducing) same wafer)) and (((carrying or	EPO; JPO;	
		introducing) same wafer) same (die near4 bond\$4)))) and	DERWENT:	
[stack\$4	IBM_TDB	
-	2	("6602773").PN.	USPAT;	2003/10/18 15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
L	<u> </u>		I IDIAI I DB	L

-	4	("5863835" "6001660" "6011311" "6066559").PN.	USPAT	2003/10/18 15:00
-	481	438/109.ccls.	USPAT;	2003/10/18 15:19
			US-PGPUB:	
1			EPO; JPO;	
			DERWENT:	
}	1	Language I. Langua	IBM_TDB	
-	4	438/109.ccls. and ((die or chip or device or semiconductor)	USPAT;	2003/10/18 15:20
	1	near4 (bonder))	US-PGPUB;	
	1		EPO; JPO;	
	1		DERWENT:	į
	}		IBM TDB	
_	145296	438/\$.ccls.	USPAT:	2003/11/25 10:22
	140200	1 400/\$.0013.	'	2003/11/23 10.22
1			US-PGPUB;	
			EPO; JPO;	
1	1		DERWENT;	
	1		IBM_TDB	
-	241	438/\$.ccls. and ((die or chip or substrate or semiconductor)	USPAT:	2003/11/25 12:01
	1	near3 bonder)	US-PGPUB;	
1			EPO; JPO;	
}	1			
1			DERWENT;	
	1		IBM_TDB	
-	23	(438/\$.ccls. and ((die or chip or substrate or semiconductor)	USPAT;	2003/11/25 10:37
		near3 bonder)) and ((die or chip or substrate or	US-PGPUB;	
1	ļ	semiconductor) near3 stack\$4)	EPO; JPO;	
		,	DERWENT:	
	ļ		IBM TDB	i
	400	400/450		0000144105 40:05
-	422	438/458.ccls.	USPAT;	2003/11/25 10:35
,	l		US-PGPUB;	1
	l		EPO; JPO;	
			DERWENT:	ļ
	j		IBM TDB	1
_	59	438/458.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 12:01
i -	33			2003/11/23 12:01
		semiconductor) near3 stack\$4)	US-PGPUB;	
	,		EPO; JPO;	
	Ì		DERWENT;	
			IBM_TDB	
-	2	(438/458.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 11:44
		semiconductor) near3 stack\$4)) and ((die or chip or substrate	US-PGPUB;	
		or semiconductor) near3 bonder)	EPO; JPO;	
		S. SSSinductory floure boridary	DERWENT:	
1				
1		(400/450th + (/);	IBM_TDB	000044405 44:40
-	57		USPAT;	2003/11/25 11:43
1		semiconductor) near3 stack\$4)) not ((438/458.ccls. and ((die	US-PGPUB;	
1		or chip or substrate or semiconductor) near3 stack\$4)) and	EPO; JPO;	
1		((die or chip or substrate or semiconductor) near3 bonder))	DERWENT;	
1		· ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	IBM TDB	
_	1218	438/118,119.ccls.	USPAT;	2003/11/25 11:44
(1210	100/110,110,000	US-PGPUB:	2000/11/20 11.77
1			,	
			EPO; JPO;	
·	1		DERWENT;	
			IBM_TDB	
[-	36	438/118,119.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 11:48
		semiconductor) near3 bonder)	US-PGPUB;	
	İ	· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT:	
<u>į</u>			•	
[IBM_TDB	
-	21	(438/118,119 ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 11:48
		semiconductor) near3 bonder)) and wafer	US-PGPUB;	
1			EPO; JPO;	
	İ		DERWENT:	
1			IBM_TDB	
L	L	I	םטו ויינטי	لــــــــــــــــــــــــــــــــــــ

-	672	438/455.ccls.	USPAT;	2003/11/25 11:48
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	8	438/455.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 11:51
	1	semiconductor) near3 bonder)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2479	438/460-465.ccls.	USPAT;	2003/11/25 11:51
1			US-PGPUB;	
1	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	21	438/460-465 ccls, and ((die or chip or substrate or	USPAT;	2003/11/25 12:28
ţ.		semiconductor) near3 bonder)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2458	438/460-465.ccls. not (438/460-465.ccls. and ((die or chip or	USPAT;	2003/11/25 11:55
İ		substrate or semiconductor) near3 bonder))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	90	(USPAT;	2003/11/25 12:01
		substrate or semiconductor) near3 bonder))) and ((die or chip	US-PGPUB;	
		or substrate or semiconductor) near3 stack\$4)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	104462	156/\$.ccls.	USPAT;	2003/11/25 12:01
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		4500	IBM_TDB	
-	75	156/\$.ccls. and ((die or chip or substrate or semiconductor)	USPAT;	2003/11/25 12:01
		near3 bonder)	US-PGPUB;	
1	1		EPO; JPO;	
	1		DERWENT;	
		(450)	IBM_TDB	0000111/05 10 5
1 -	3	(156/\$.ccls. and ((die or chip or substrate or semiconductor)	USPAT;	2003/11/25 12:05
		near3 bonder)) and ((die or chip or substrate or	US-PGPUB;	
		semiconductor) near3 stack\$4)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	79	((438/460-465.ccls. not (438/460-465.ccls. and ((die or chip	USPAT;	2003/11/25 12:06
		or substrate or semiconductor) near3 bonder))) and ((die or	US-PGPUB;	
		chip or substrate or semiconductor) near3 stack\$4)) and	EPO; JPO;	
	1	wafer	DERWENT;	
	<u> </u>		IBM_TDB	